In the Claims:

1. (Currently amended) A semiconductor laser, comprising:

~~characterized in that~~

~~it contains~~ at least one absorbing layer (8) within the laser resonator, said absorbing layer reducing the transmission T_{Res} of the laser radiation (10) in the laser resonator for the purpose of decreasing the sensitivity of the semiconductor laser to disturbances created by the radiation (9) fed back into the laser resonator.

2. (Original) The semiconductor laser as claimed in claim 1,

in which the absorbing layer (8) is situated in a node of a standing wave that forms during operation of the semiconductor laser in the laser resonator.

3. (Currently amended) The semiconductor laser as claimed in claim 1 ~~or 2~~, in which the reflectivity of the mirrors of the resonator and the transmission T_{Res} of the laser radiation during a resonator circulation are set so as to produce a low sensitivity to disturbances for a wide range of possible output powers of the semiconductor laser.

4. (Currently amended) The semiconductor laser as claimed in claim 1 ~~one of claims 1 to 3~~, in which the semiconductor laser is a single-mode laser.

5. (Currently amended) The semiconductor laser as claimed in claim 1 ~~one of claims 1 to 4~~, in which the semiconductor laser is a surface emitting semiconductor laser (VCSEL).

6. (Currently amended) The semiconductor laser as claimed in claim 1 ~~one of claims 1 to 4~~, in which the semiconductor laser is a surface emitting semiconductor laser with an external resonator (VECSEL).

7. (Currently amended) The semiconductor laser as claimed in claim ~~5 or~~ 6, in which the surface emitting semiconductor laser contains a Bragg mirror (4) and the absorbing layer (8) is contained in said Bragg mirror (4).

8. (Currently amended) The semiconductor laser as claimed in claim 1 ~~one of claims 1 to 7~~,

in which the absorbing layer (8) is a gallium arsenide layer.

9. (Currently amended) The semiconductor laser as claimed in claim 1 ~~one of claims 1 to 8~~, in which the gallium arsenide layer is approximately 20 nm thick.

10. (Currently amended) The semiconductor laser as claimed in claim 1 ~~one of claims 1 to 9~~, which contains a plurality of absorbing layers within the laser resonator.

11. (New) The semiconductor laser as claimed in claim 5, in which the surface emitting semiconductor laser contains a Bragg mirror (4) and the absorbing layer (8) is contained in said Bragg mirror (4).